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PATENT ABSTRACTS OF JAPAN(21) Application number: **60006470**(51) Int. Cl.: **H01L 29/78 G11C 17/00**(22) Application date: **17.01.85**

(30) Priority:

(43) Date of application
publication: **26.07.86**(71) Applicant: **MATSUSHITA ELECTRONICS CORP**(72) Inventor: **ARIGA RIE**

(74) Representative:

**(54) FLOATING-GATE TYPE
NONVOLATILE MEMORY
ELEMENT**

(57) Abstract:

PURPOSE: To not only project ultraviolet rays but also enable an erasing electrically on the erasing by combining a diode with a floating-gate.

CONSTITUTION: A diode is combined with a floating-gate. Consequently, when a diode 7 for the floating-gate section is biassed in the opposite direction, only a memory element section is effective in the floating-gate 4, and charges can be stored temporarily as a floating-gate type nonvolatile memory element. When the floating-gate 4 section is biassed in the forward direction, on the contrary, charges stored in the memory element section can be discharged.

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